# INTEGRATED CIRCUITS

# DATA SHEET

# 74ABT16260

12-bit to 24-bit multiplexed D-type latch (3-State)

Product data Replaces 74ABT16260/74ABTH16260 dated 1998 Feb 10





# 12-bit to 24-bit multiplexed D-type latch (3-State)

74ABT16260

#### **FEATURES**

- ESD protection exceeds 2000 V per Mil-Std-883C, Method 3015; exceeds 200 V using machine model (C = 200 pF, R = 0).
- Latch-up performance exceeds 500 mA per JEDEC Standard JESD-17.
- Distributed V<sub>CC</sub> and GND pin configuration minimizes high-speed switching noise.
- Flow-through architecture optimizes PCB layout.
- High-drive outputs (-32 mA I<sub>OH</sub>, 64 mA I<sub>OL</sub>).
- Package options:
  - 56-pin plastic Shrink Small-Outline Package (SSOP)
  - 56-pin plastic Thin Shrink Small-Outline Package (TSSOP)

#### **DESCRIPTION**

The 74ABT16260 is a 12-bit to 24-bit multiplexed D-type latch used in applications where two separate data paths must be multiplexed onto, or demultiplexed from, a single data path. Typical applications include multiplexing and/or demultiplexing of address and data information in microprocessor or bus-interface applications. This device is also useful in memory-interleaving applications.

Three 12-bit I/O ports (A1–A12, 1B1–1B12, and 2B1–2B12) are available for address and/or data transfer. The output enable ( $\overline{OE1B}$ ,  $\overline{OE2B}$ , and  $\overline{OEA}$ ) inputs control the bus transceiver functions. The  $\overline{OE1B}$  and  $\overline{OE2B}$  control signals also allow bank control in the A-to-B direction.

Address and/or data information can be stored using the internal storage latches. The latch enable (LE1B, LE2B, LEA1B, and LEA2B) inputs are used to control data storage. When the latch enable input is HIGH, the latch is transparent. When the latch enable input goes LOW, the data present at the inputs is latched and remains latched until the latch enable input is returned HIGH.

To ensure the high-impedance state during power-up or power-down,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pull-up resistor; the minimum value of the resistor is determined by the current sinking capability of the driver.

### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	CONDITIONS T <sub>amb</sub> = 25°C; GND = 0V	TYPICAL	UNIT
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay nAx to nBx nBx to nAx	C <sub>L</sub> = 50 pF	2.8 2.5	ns
C <sub>IN</sub>	Input capacitance	$V_I = 0 \text{ V or } V_{CC}$	4	pF
C <sub>OUT</sub>	Output capacitance	V <sub>I/O</sub> = 0 V or 5.0 V	6	pF
I <sub>CCZ</sub>	Total supply current	Outputs disabled	100	μΑ

### ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	ORDER CODE	DWG NUMBER
56-Pin Plastic SSOP Type III	–40 °C to +85 °C	74ABT16260DL	SOT371-1
56-Pin Plastic TSSOP Type II	–40 °C to +85 °C	74ABT16260DGG	SOT364-1

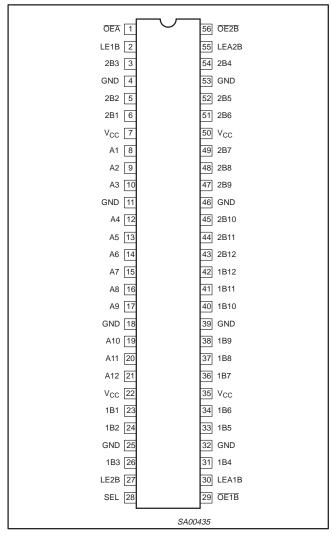
### PIN DESCRIPTION

PIN NUMBER	SYMBOL	FUNCTION			
8, 9, 10, 12, 13, 14, 15, 16, 17, 19, 20, 21	An	Data inputs/outputs (A)			
23, 24, 26, 31, 33, 34, 36, 37, 38, 40, 41, 42	1Bn	Data inputs/outputs (B1)			
6, 5, 3, 54, 52, 51, 49, 48, 47, 45, 44, 43	2Bn	Data inputs/outputs (B2)			
1, 29, 56	OEA, OE1B, OE2B	Output enable input (Active-LOW)			
2, 27, 30, 55	LE1B, LE2B, LEA1B, LEA2B	Latch enable inputs			

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### **PIN CONFIGURATION**



### **FUNCTION TABLES**

# B to A ( $\overline{OEB} = H$ )

		INP	UTS			OUTPUT
1B	2B	SEL	LE1B	LE2B	OEA	Α
Н	Х	Н	Н	Х	L	Н
L	Х	Н	Н	Х	L	L
X	Х	Н	L	Х	L	A0
Х	Н	L	Х	Н	L	Н
X	L	L	Х	Н	L	L
X	Х	L	Х	L	L	A0
Х	Х	Х	Х	Х	Н	Z

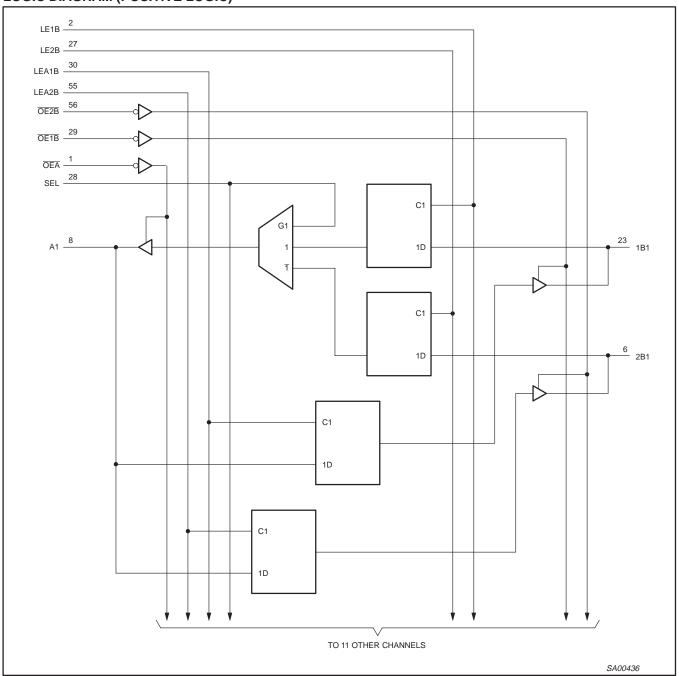
# A to B ( $\overline{OEA} = H$ )

		INPUTS			OUT	PUT
Α	LEA1B	LEA2B	OE1B	OE2B	1B	2B
Н	Н	Н	L	L	Н	Н
L	Н	Н	L	L	L	L
н	н	L	L	L	Н	2B0
L	Н	L	L	L	L	2B0
н	L	н	L	L	1B0	Н
L	L	Н	L	L	1B0	L
x	L	L	L	L	1B0	2B0
x	Х	Х	Н	Н	Z	Z
x	Х	Х	L	Н	Active	Z
x	Х	Х	Н	L	Z	Active
X	Х	Х	L	L	Active	Active

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# **LOGIC DIAGRAM (POSITIVE LOGIC)**



# 12-bit to 24-bit multiplexed D-type latch (3-State)

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#### ABSOLUTE MAXIMUM RATINGS

Over operating free-air temperature range (unless otherwise specified)<sup>1</sup>

SYMBOL	PARAMETER	CONDITIONS	LIM	ITS	UNIT	
STWIBUL	PARAMETER	CONDITIONS	MIN	MAX	ONT	
V <sub>CC</sub>	Supply voltage range		-0.5	7	V	
VI	Input voltage range	see Note 2	-0.5	7	V	
Vo	Voltage range applied to any output in the HIGH state or power-off state		-0.5	5.5	V	
Io	Current into any output in the LOW state		-	128	mA	
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0	ı	-18	mA	
l <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0	1	-50	mA	
	Maximum power dissipation at T <sub>amb</sub> = 55 °C (in still air)	see Note 3	_	1.4	W	
T <sub>stg</sub>	Storage temperature range		-65	+150	°C	

#### NOTES:

- 1. Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.
- The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
   The maximum package power dissipation is calculated using a junction temperature of 150 °C and a board trace length of 750 mils.

### RECOMMENDED OPERATING CONDITIONS<sup>1</sup>

SYMBOL	PARAMETER	LIM	UNIT		
STWIDUL	PARAMETER		MIN	MAX	UNII
V <sub>CC</sub>	Supply voltage		4.5	5.5	V
V <sub>IH</sub>	HIGH-level input voltage		2	_	V
V <sub>IL</sub>	LOW-level input voltage	_	0.8	V	
V <sub>I</sub>	Input voltage		0	V <sub>CC</sub>	V
I <sub>OH</sub>	HIGH-level output current		ı	-32	mA
I <sub>OL</sub>	LOW-level output current		-	64	mA
ΔtΔ/ν	Input transition rise or fall rate	Outputs enabled	ı	10	ns/V
ΔtΔ/V <sub>CC</sub>	Power-up ramp rate		200	1	μs/V
T <sub>amb</sub>	Operating free-air temperature		-40	+85	°C

### NOTE:

1. Unused or floating inputs must be held HIGH or LOW.

# 12-bit to 24-bit multiplexed D-type latch (3-State)

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# DC ELECTRICAL CHARACTERISTICS

						LIMITS			
SYMBOL	PARAMETER	TEST CONDITION:	T <sub>ar</sub>	<sub>nb</sub> = +25	°C		–40 °C 35 °C	UNIT	
				Min	Тур	Max	Min	Max	
$V_{IK}$	Input clamp voltage	$V_{CC} = 4.5 \text{ V}; I_{IK} = -18 \text{ mA}$		_	-0.8	-1.2	_	-1.2	V
		$V_{CC} = 4.5 \text{ V}; I_{OH} = -3 \text{ mA}; V_{I} =$	V <sub>IL</sub> or V <sub>IH</sub>	2.5	2.9	-	2.5	-	V
V <sub>OH</sub>	HIGH-level output voltage	$V_{CC} = 5.0 \text{ V}; I_{OH} = -3 \text{ mA}; V_{I} =$	V <sub>IL</sub> or V <sub>IH</sub>	3.0	3.4	-	3.0	-	V
		$V_{CC} = 4.5 \text{ V}; I_{OH} = -32 \text{ mA}; V_{I} =$	= V <sub>IL</sub> or V <sub>IH</sub>	2.0	2.4	-	2.0	-	V
$V_{OL}$	LOW-level output voltage	$V_{CC} = 4.5 \text{ V}; I_{OL} = 64 \text{ mA}; V_{I} = 7$	V <sub>IL</sub> or V <sub>IH</sub>	-	0.42	0.55	-	0.55	V
I	Input leakage current	$V_{CC} = 5.5 \text{ V}; V_I = V_{CC} \text{ or GND}$	_	±0.01	±1	_	±1	μА	
		$V_{CC} = 5.5 \text{ V}; V_{I} = V_{CC} \text{ or GND}$ Data pins				±3	-	±5	μΑ
l <sub>OFF</sub>	Power-off leakage current	$V_{CC} = 0.0 \text{ V}$ ; $V_O \text{ or } V_I \le 4.5 \text{ V}$		-	±5.0	±100	-	±100	μΑ
I <sub>PU</sub> /I <sub>PD</sub>	Power-up/down 3-State output current	$V_{CC} = 2.0 \text{ V}; V_{O} = 0.5 \text{ V}; V_{I} = \text{GND or } V_{CC}; V_{OE} = V_{CC}$		-	±60	±200	_	±200	μА
I <sub>OZH</sub>	3-State output HIGH current	$V_{CC} = 5.5 \text{ V}; V_{O} = 2.7 \text{ V}; V_{I} = V_{I}$	<sub>IL</sub> or V <sub>IH</sub>	-	1.0	10	-	10	μΑ
I <sub>OZL</sub>	3-State output LOW current	$V_{CC} = 5.5 \text{ V}; V_{O} = 0.5 \text{ V}; V_{I} = V_{I}$	<sub>IL</sub> or V <sub>IH</sub>	-	-1.0	-10	_	-10	μΑ
I <sub>CEX</sub>	Output HIGH leakage current	$V_{CC} = 5.5 \text{ V}; V_{O} = 5.5 \text{ V}; V_{I} = G$	ND or V <sub>CC</sub>	_		50	_	50	μΑ
Io	Output current <sup>1</sup>	$V_{CC} = 5.5 \text{ V}; V_{O} = 2.5 \text{ V}$		-50	-100	-225	-50	-225	mA
		$V_{CC} = 5.5 \text{ V};$ Outputs HIGH, $V_I = \text{GND or } V_{CI}$	С	_	0.2	1.5	_	1.5	mA
Icc	Quiescent supply current	$V_{CC} = 5.5 \text{ V};$ Outputs LOW, $V_I = \text{GND}$ or $V_{CC}$	<b>)</b>	-	8	19	_	19	mA
		$V_{CC} = 5.5 \text{ V};$ Outputs 3-State; $V_I = \text{GND}$ or V	-	0.1	1.0	_	1.0	mA	
Δl <sub>CC</sub>	Additional supply current per input pin <sup>2</sup>	Outputs enabled, one input at 3 inputs at $V_{CC}$ or GND; $V_{CC} = 5$ .		-	0.1	1.5	_	1.5	mA

# NOTES:

<sup>1.</sup> Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

<sup>2.</sup> This is the increase in supply current for each input that is at the specified TTL voltage level rather than  $V_{CC}$  or GND.

# 12-bit to 24-bit multiplexed D-type latch (3-State)

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### **AC ELECTRICAL CHARACTERISTICS**

Over recommended operating free-air temperature range (unless otherwise noted).

CVMDOL	PARAI	METER	V <sub>CC</sub> :	= 5 V; T <sub>amb</sub> =	25 °C	T <sub>amb</sub> = -40	°C to +85 °C	UNIT
SYMBOL	FROM (INPUT)	TO (OUTPUT)	MIN	TYP	MAX	MIN	MAX	UNII
t <sub>PLH</sub>	A or B	B or A	1	2.8	4.8	1	5.6	ns
t <sub>PHL</sub>	AUIB	BUIA	1	2.5	5	1	5.9	ns
t <sub>PLH</sub>	ΙĒ	A or B	1.1	3.2	4.9	1.1	5.8	ns
t <sub>PHL</sub>	LE	AUIB	1.1	3.2	4.9	1.1	5.3	ns
	SEL (B1)	А	1.3	3.2	4.6	1.3	5.3	ns
t <sub>PLH</sub>	SEL (B2)	А	1.1	2.8	4.9	1.1	6	ns
	SEL (B1)	А	1.5	3.0	4.4	1.5	4.4	ns
t <sub>PHL</sub>	SEL (B2)	А	1.6	2.6	5.1	1.6	5.9	ns
t <sub>PZH</sub>	ŌĒ	A 0 * D	1	2.9	4.7	1	5.7	ns
t <sub>PZL</sub>	OE	A or B	1.6	2.2	5.1	1.6	5.8	ns
t <sub>PHZ</sub>	OΕ	A or D	2.2	4.1	5.4	2.2	6.4	ns
t <sub>PLZ</sub>	ŌĒ	A or B	1.3	3.2	4.4	1.3	4.8	ns

# **AC SETUP CHARACTERISTICS**

Over recommended operating free-air temperature range (unless otherwise noted).

SYMBOL	PARAMETER	V <sub>CC</sub> = 5 V; T	<sub>amb</sub> = 25 °C	T <sub>amb</sub> = -40 °	UNIT	
	PARAMETER	MIN	MAX	MIN	MAX	UNIT
t <sub>w</sub>	Pulse duration, LE1B, LE2B, LEA1B, or LEA2B HIGH	3.3	_	3.3	-	ns
t <sub>su</sub>	Set-up time, data before LE1B, LE2B, LEA1B, or LEA2B↓	1.5	-	1.5	_	ns
t <sub>h</sub>	Hold time, data after LE1B, LE2B, LEA1B, or LEA2B↓	1	-	1	-	ns

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#### **AC WAVEFORMS**

V<sub>M</sub> = 1.5 V for all waveforms

The outputs are measured one at a time with one transition per measurement.

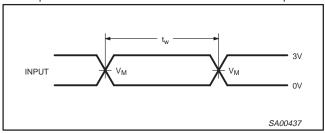


Figure 1. Pulse duration

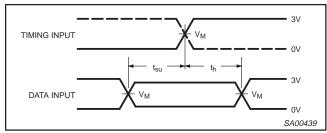
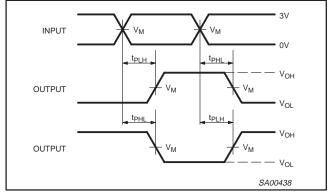
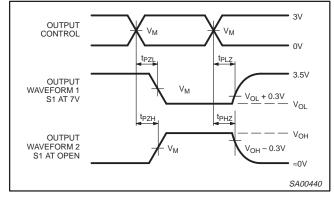


Figure 3. Set-up and hold times



All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O=50~\Omega,~t_f\leq 2.5$  ns,  $t_f\leq 2.5$  ns.

Figure 2. Propagation delay times; inverting and non-inverting outputs



Waveform 1 is for an output with internal conditions such that the output is LOW except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is HIGH except when disabled by the output control.

Figure 4. Enable and disable times; LOW- and HIGH-level enabling

## **TEST LOAD CIRCUIT**

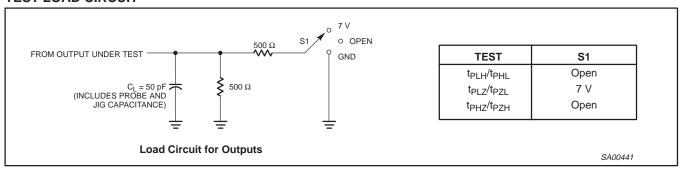


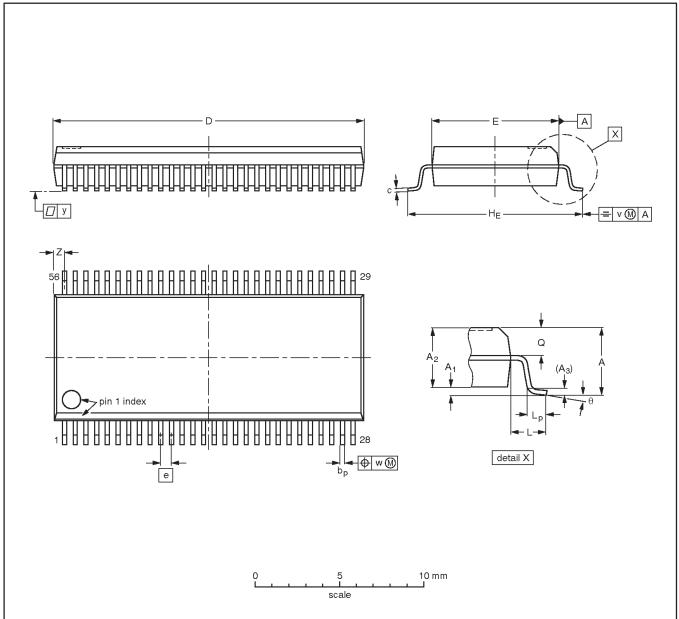
Figure 5. Test load circuit

# 12-bit to 24-bit multiplexed D-type latch (3-State)

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# SSOP56: plastic shrink small outline package; 56 leads; body width 7.5 mm

SOT371-1



### DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	2.8	0.4 0.2	2.35 2.20	0.25	0.3 0.2	0.22 0.13	18.55 18.30	7.6 7.4	0.635	10.4 10.1	1.4	1.0 0.6	1.2 1.0	0.25	0.18	0.1	0.85 0.40	8° 0°

#### Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

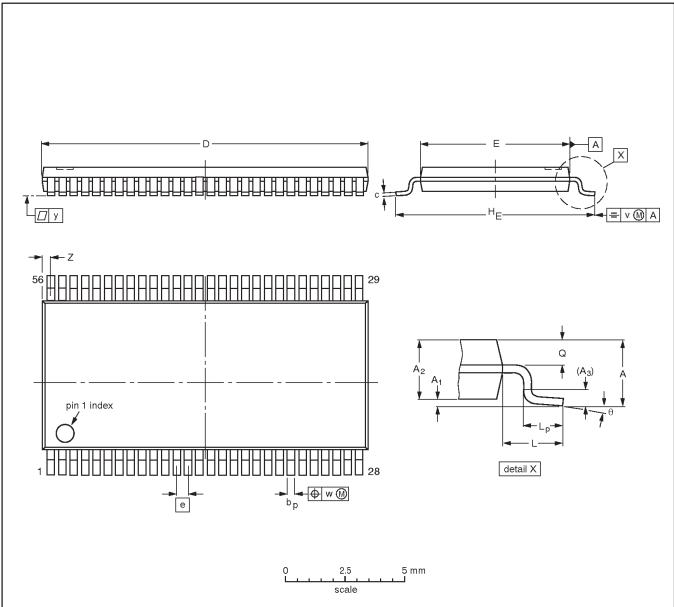
OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT371-1		MO-118				<del>95-02-04</del> 99-12-27

# 12-bit to 24-bit multiplexed D-type latch (3-State)

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# TSSOP56: plastic thin shrink small outline package; 56 leads; body width 6.1 mm

SOT364-1



#### DIMENSIONS (mm are the original dimensions).

UNIT	A max.	Α1	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	L	Lp	Q	v	w	у	Z	θ
mm	1.2	0.15 0.05	1.05 0.85	0.25	0.28 0.17	0.2 0.1	14.1 13.9	6.2 6.0	0.5	8.3 7.9	1.0	0.8 0.4	0.50 0.35	0.25	0.08	0.1	0.5 0.1	8° 0°

#### Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

	OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE	
	SOT364-1		MO-153				<del>-95-02-10-</del> 99-12-27

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**NOTES** 

# 12-bit to 24-bit multiplexed D-type latch (3-State)

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#### Data sheet status

Data sheet status <sup>[1]</sup>	Product status <sup>[2]</sup>	Definitions
Objective data	Development	This data sheet contains data from the objective specification for product development.  Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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<sup>[1]</sup> Please consult the most recently issued data sheet before initiating or completing a design.

#### **Definitions**

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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